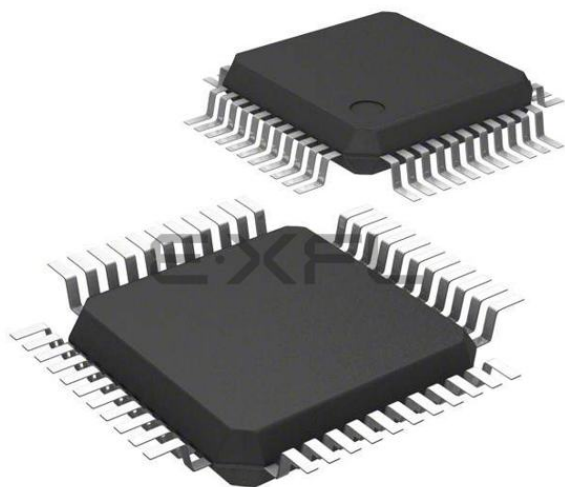




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101fgdfp-50

Table 1-1. List of Ordering Part Numbers

(5/12)

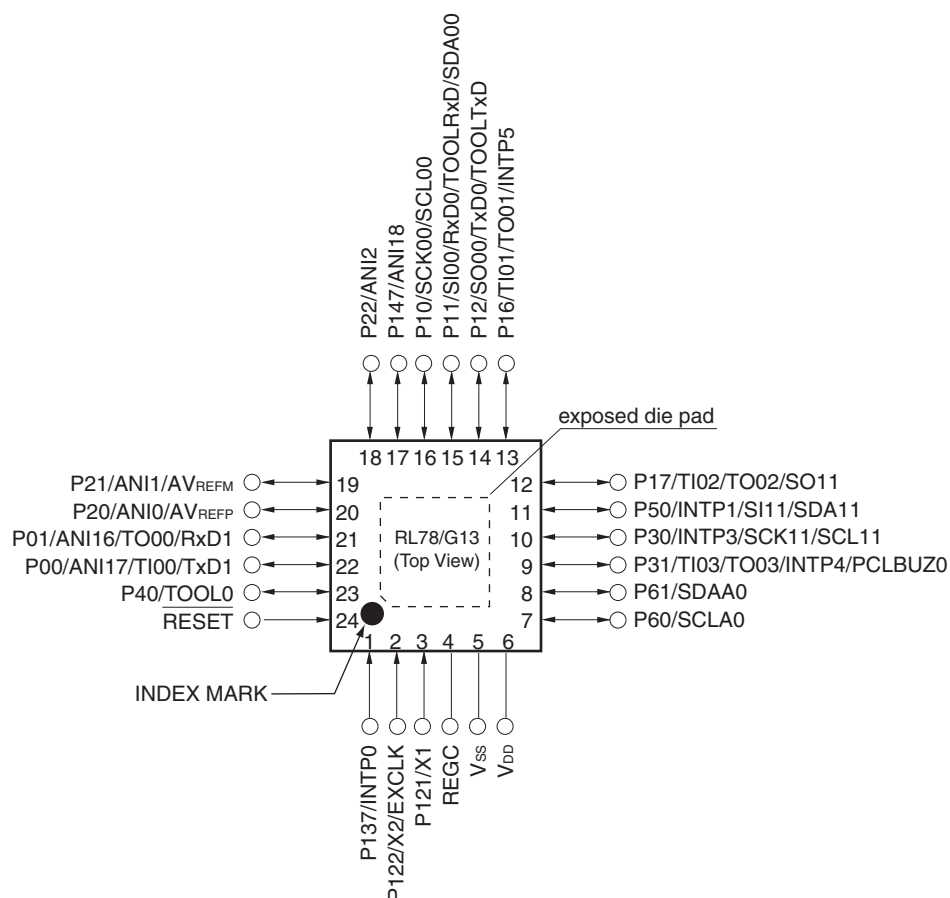
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	Mounted	A	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0, R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0, R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0, R5F100GLAFB#V0 R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0, R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0, R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0, R5F100GLAFB#X0
			D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0, R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0, R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0, R5F100GLDFB#V0 R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0, R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0, R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0, R5F100GLDFB#X0
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0, R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0, R5F100GHGFB#V0, R5F100GJGFB#V0 R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0, R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0, R5F100GHGFB#X0, R5F100GJGFB#X0
		Not mounted	A	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0, R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0, R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0, R5F101GLAFB#V0 R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0, R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0, R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0, R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0, R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0, R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0, R5F101GLDFB#V0 R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0, R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0, R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0, R5F101GLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.2 24-pin products

- 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



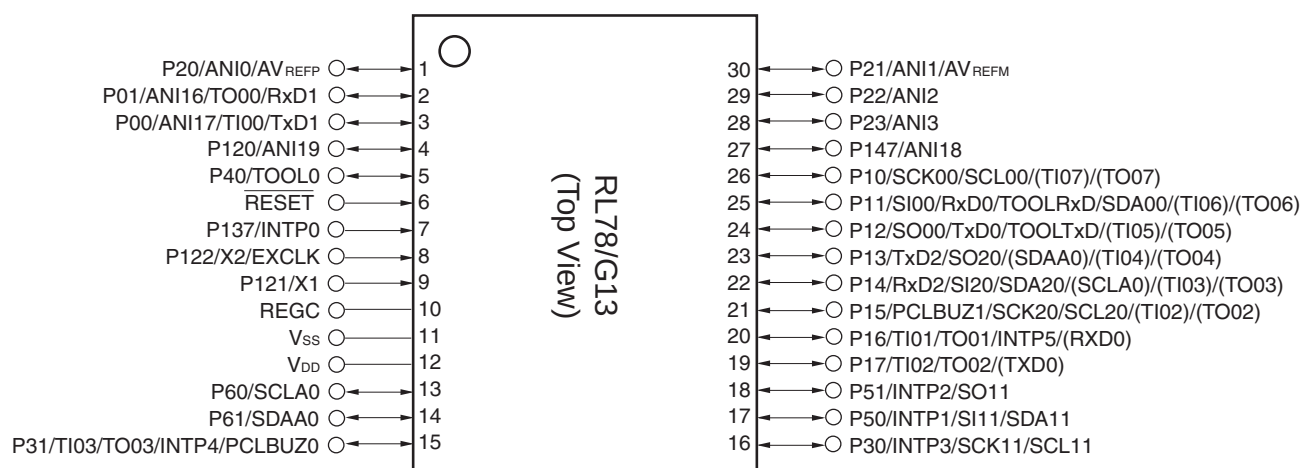
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. It is recommended to connect an exposed die pad to Vss.

1.3.4 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



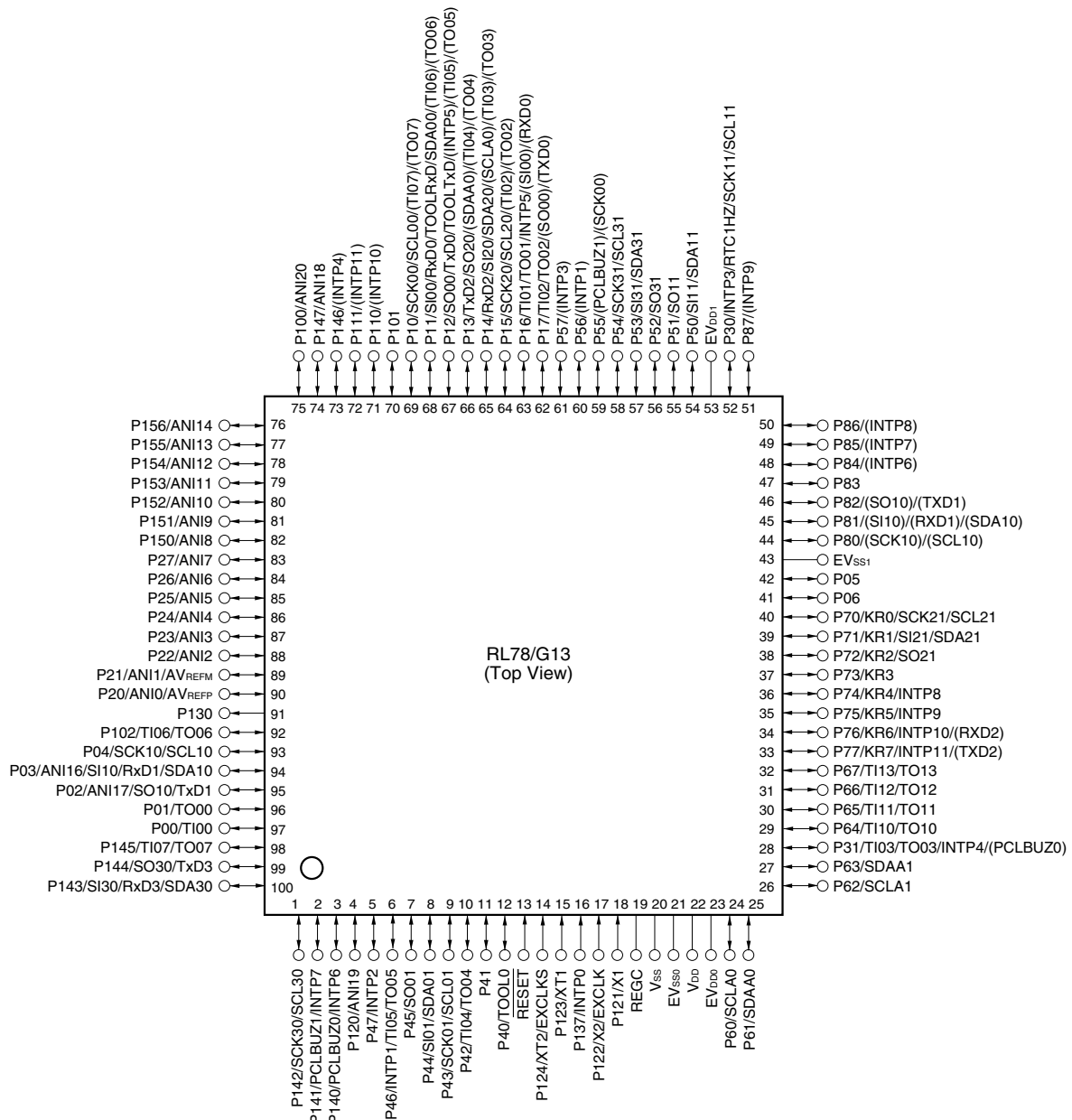
Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.13 100-pin products

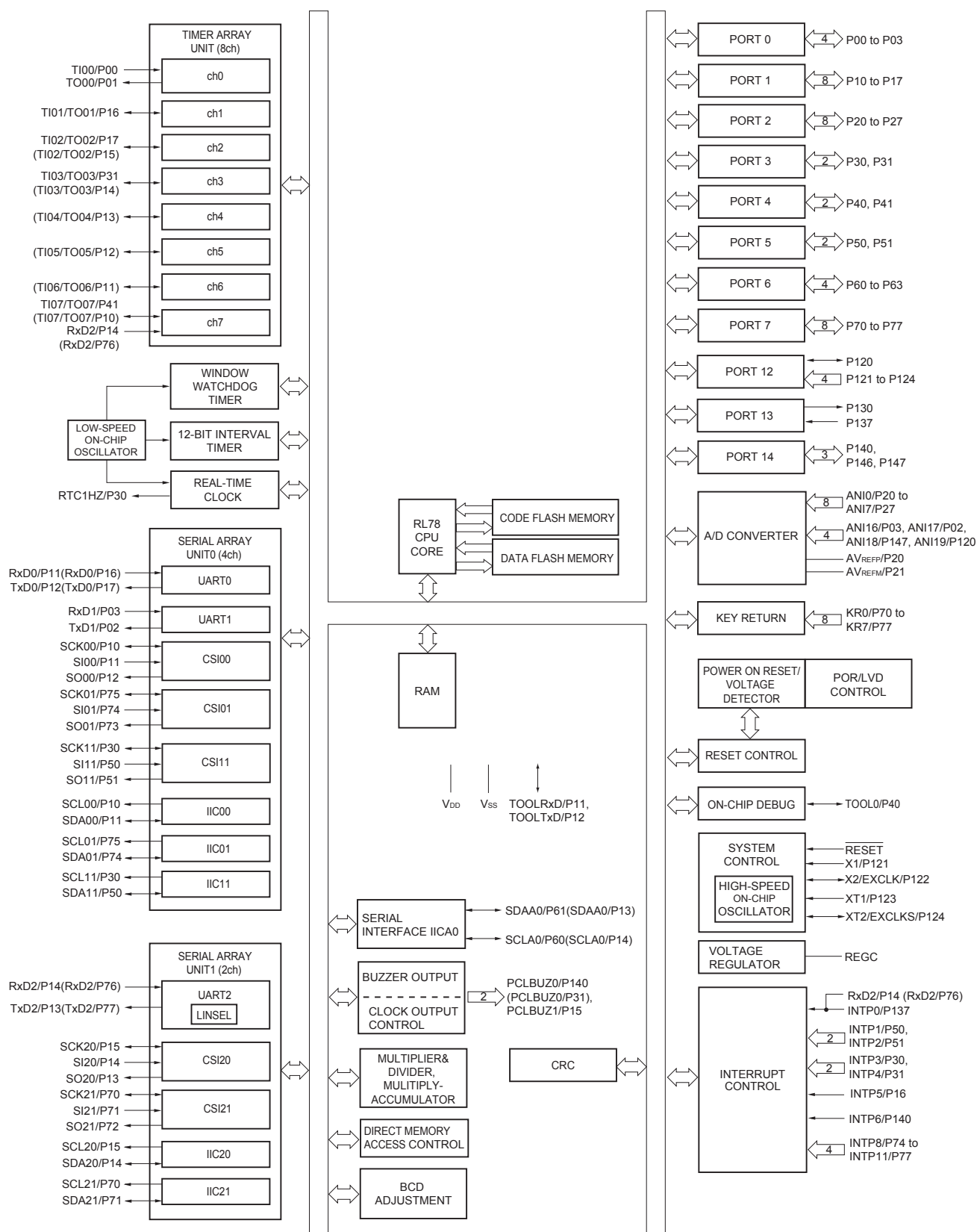
- 100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)



- Cautions**
1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.10 52-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

(T_A = -40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f _x) ^{Note}	Ceramic resonator/ crystal resonator	2.7 V ≤ V _{DD} ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V	1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V	1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V	1.0		4.0	MHz
XT1 clock oscillation frequency (f _x) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator.

2.2.2 On-chip oscillator characteristics

(T_A = -40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	f _{IH}			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to +85 °C	1.8 V ≤ V _{DD} ≤ 5.5 V	-1.0		+1.0	%
			1.6 V ≤ V _{DD} < 1.8 V	-5.0		+5.0	%
		-40 to -20 °C	1.8 V ≤ V _{DD} ≤ 5.5 V	-1.5		+1.5	%
			1.6 V ≤ V _{DD} < 1.8 V	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	f _{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.62	1.86	mA	
					V _{DD} = 3.0 V		0.62	1.86	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.45	mA	
					V _{DD} = 3.0 V		0.50	1.45	mA	
					f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.11	mA
						V _{DD} = 3.0 V		0.44	1.11	mA
				LS (low-speed main) mode Note 7	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		290	620	μA
						V _{DD} = 2.0 V		290	620	μA
				LV (low-voltage main) mode Note 7	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		440	680	μA
						V _{DD} = 2.0 V		440	680	μA
			HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.31	1.08	mA	
					Resonator connection		0.48	1.28	mA	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.31	1.08	mA	
					Resonator connection		0.48	1.28	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.21	0.63	mA	
					Resonator connection		0.28	0.71	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.21	0.63	mA	
					Resonator connection		0.28	0.71	mA	
				LS (low-speed main) mode Note 7	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		110	360	μA
						Resonator connection		160	420	μA
			f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V		Square wave input		110	360	μA	
					Resonator connection		160	420	μA	
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.28	0.61	μA	
					Resonator connection		0.47	0.80	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.34	0.61	μA	
					Resonator connection		0.53	0.80	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	2.30	μA	
					Resonator connection		0.60	2.49	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.64	4.03	μA	
					Resonator connection		0.83	4.22	μA	
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.09	8.04	μA		
				Resonator connection		1.28	8.23	μA		
	I _{DD3} Note 6	STOP mode Note 8	T _A = −40°C					0.19	0.52	μA
			T _A = +25°C					0.25	0.52	μA
			T _A = +50°C					0.32	2.21	μA
			T _A = +70°C					0.55	3.94	μA
			T _A = +85°C					1.00	7.95	μA

(Notes and Remarks are listed on the next page.)

6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.
7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.
8. Current flowing only during data flash rewrite.
9. Current flowing only during self programming.
10. For shift time to the SNOOZE mode, see **18.3.3 SNOOZE mode**.

- Remarks**
1. f_{IL} : Low-speed on-chip oscillator clock frequency
 2. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 3. f_{CLK} : CPU/peripheral hardware clock frequency
 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	t _{KH2} , t _{KL2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	t _{KCY2} /2 - 12		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	t _{KCY2} /2 - 18		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
Slp setup time (to SCKp↑) ^{Note 3}	t _{SIK2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	1/f _{MCK} + 30		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
Slp hold time (from SCKp↑) ^{Note 4}	t _{KS12}		1/f _{MCK} + 31		1/f _{MCK} + 31		1/f _{MCK} + 31		ns
Delay time from SCKp↓ to SOp output ^{Note 5}	t _{KSO2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		2/f _{MCK} + 120		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		2/f _{MCK} + 214		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ		2/f _{MCK} + 573		2/f _{MCK} + 573		2/f _{MCK} + 573	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps2. Use it with EV_{DD0} ≥ V_b.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

<R>

- Notes**
1. The first clock pulse is generated after this period when the start/restart condition is detected.
 2. The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

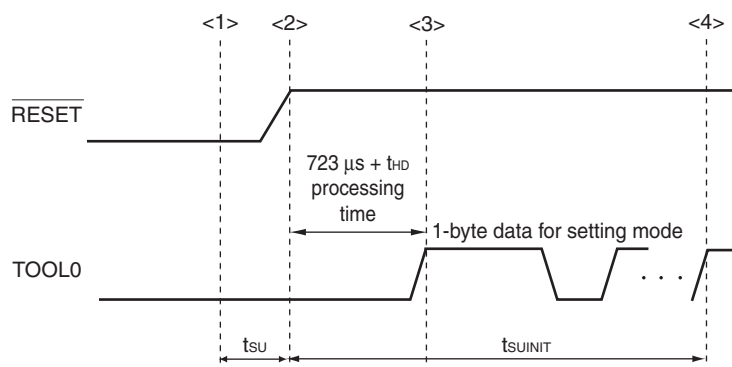
Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 kΩ

2.10 Timing of Entry to Flash Memory Programming Modes

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t _{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t _{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t _{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

3.3 DC Characteristics

3.3.1 Pin characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	I _{OH1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	2.4 V ≤ EV _{DD0} ≤ 5.5 V		-3.0 ^{Note 2}	mA
		Total of P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ EV _{DD0} ≤ 5.5 V		-30.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V		-10.0	mA
			2.4 V ≤ EV _{DD0} < 2.7 V		-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ EV _{DD0} ≤ 5.5 V		-30.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V		-19.0	mA
			2.4 V ≤ EV _{DD0} < 2.7 V		-10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ EV _{DD0} ≤ 5.5 V		-60.0	mA
	I _{OH2}	Per pin for P20 to P27, P150 to P156	2.4 V ≤ V _{DD} ≤ 5.5 V		-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ V _{DD} ≤ 5.5 V		-1.5	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

2. Do not exceed the total current value.

3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA

$$\text{Total output current of pins} = (-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.62	3.40	mA	
					V _{DD} = 3.0 V		0.62	3.40	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	2.70	mA	
					V _{DD} = 3.0 V		0.50	2.70	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.90	mA	
					V _{DD} = 3.0 V		0.44	1.90	mA	
				HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.31	2.10	mA
						Resonator connection		0.48	2.20	mA
					f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.31	2.10	mA
						Resonator connection		0.48	2.20	mA
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V		Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V		Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
			Subsystem clock operation		f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.28	0.61	μA
						Resonator connection		0.47	0.80	μA
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.34	0.61	μA	
					Resonator connection		0.53	0.80	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	2.30	μA	
					Resonator connection		0.60	2.49	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.64	4.03	μA	
					Resonator connection		0.83	4.22	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.09	8.04	μA	
					Resonator connection		1.28	8.23	μA	
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +105°C	Square wave input		5.50	41.00	μA		
				Resonator connection		5.50	41.00	μA		
	I _{DD3} ^{Note 6}	STOP mode ^{Note 8}	T _A = −40°C					0.19	0.52	μA
			T _A = +25°C					0.25	0.52	μA
			T _A = +50°C					0.32	2.21	μA
			T _A = +70°C					0.55	3.94	μA
			T _A = +85°C					1.00	7.95	μA
			T _A = +105°C					5.00	40.00	μA

(Notes and Remarks are listed on the next page.)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate		Reception	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$		$f_{MCK}/12$ ^{Note 1}	bps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$		2.6	Mbps
			$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$		$f_{MCK}/12$ ^{Note 1}	bps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$		2.6	Mbps
			$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$		$f_{MCK}/12$ ^{Notes 1,2}	bps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$		2.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2.** The following conditions are required for low voltage interface when $EV_{DD0} < V_{DD}$.
 $2.4\text{ V} \leq EV_{DD0} < 2.7\text{ V}$: MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Remarks 1. $V_b[V]$: Communication line voltage**2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)**3.** f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)**

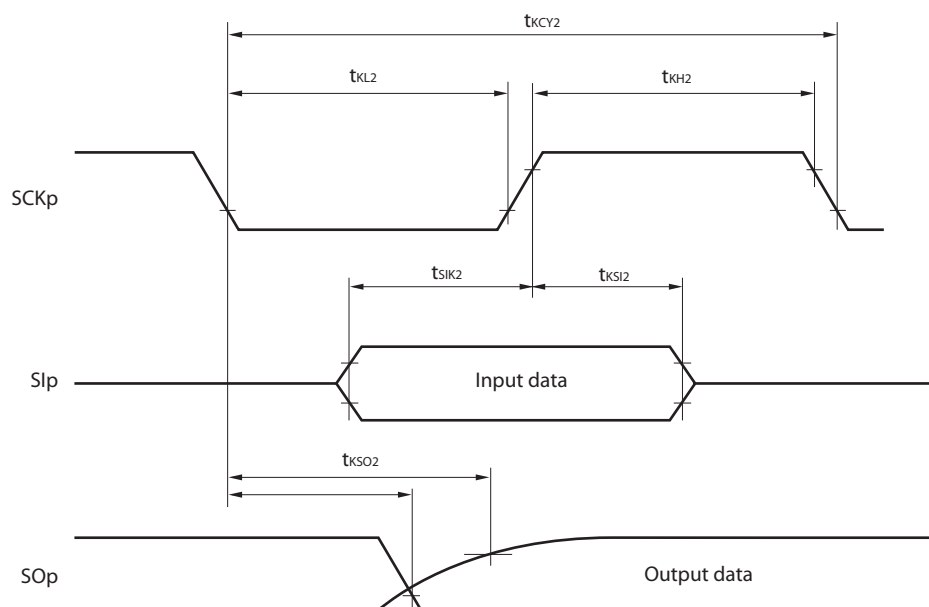
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp $\uparrow$) ^{Note}	t_{SIK1}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	162		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	354		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	958		ns
Slp hold time (from SCKp $\uparrow$) ^{Note}	t_{KSI1}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	38		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	38		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	38		ns
Delay time from SCKp $\downarrow$ to SOp output ^{Note}	t_{KSO1}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$		200	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$		390	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$		966	ns

Note When $\text{DAPmn} = 0$ and $\text{CKPmn} = 0$, or $\text{DAPmn} = 1$ and $\text{CKPmn} = 1$.

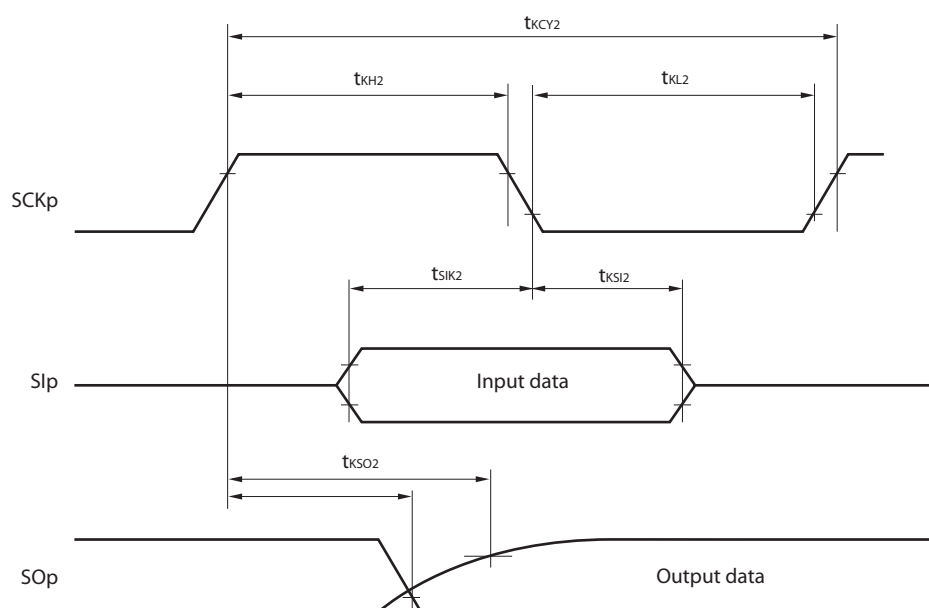
Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,
 n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
- 2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
 Use other CSI for communication at different potential.

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (-) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (-) = AV_{REFM}
ANI0 to ANI14	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI26	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1).		—

(1) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		1.2	± 3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2 to ANI14	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E_{ZS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 0.25	%FSR
Full-scale error ^{Notes 1, 2}	E_{FS}	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 2.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 1.5	LSB
Analog input voltage	V_{AIN}	ANI2 to ANI14		0		AV_{REFP}	V
		Internal reference voltage output ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 4}			V

(Notes are listed on the next page.)

3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode**($T_A = -40$ to $+105^\circ\text{C}$, $V_{PDR} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V _{LVD0}	Power supply rise time	3.90	4.06	4.22	V
			Power supply fall time	3.83	3.98	4.13	V
		V _{LVD1}	Power supply rise time	3.60	3.75	3.90	V
			Power supply fall time	3.53	3.67	3.81	V
		V _{LVD2}	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		V _{LVD3}	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		V _{LVD4}	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		V _{LVD5}	Power supply rise time	2.70	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		V _{LVD6}	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		V _{LVD7}	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width		t _{LW}		300			μs
Detection delay time						300	μs

LVD Detection Voltage of Interrupt & Reset Mode**($T_A = -40$ to $+105^\circ\text{C}$, $V_{PDR} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

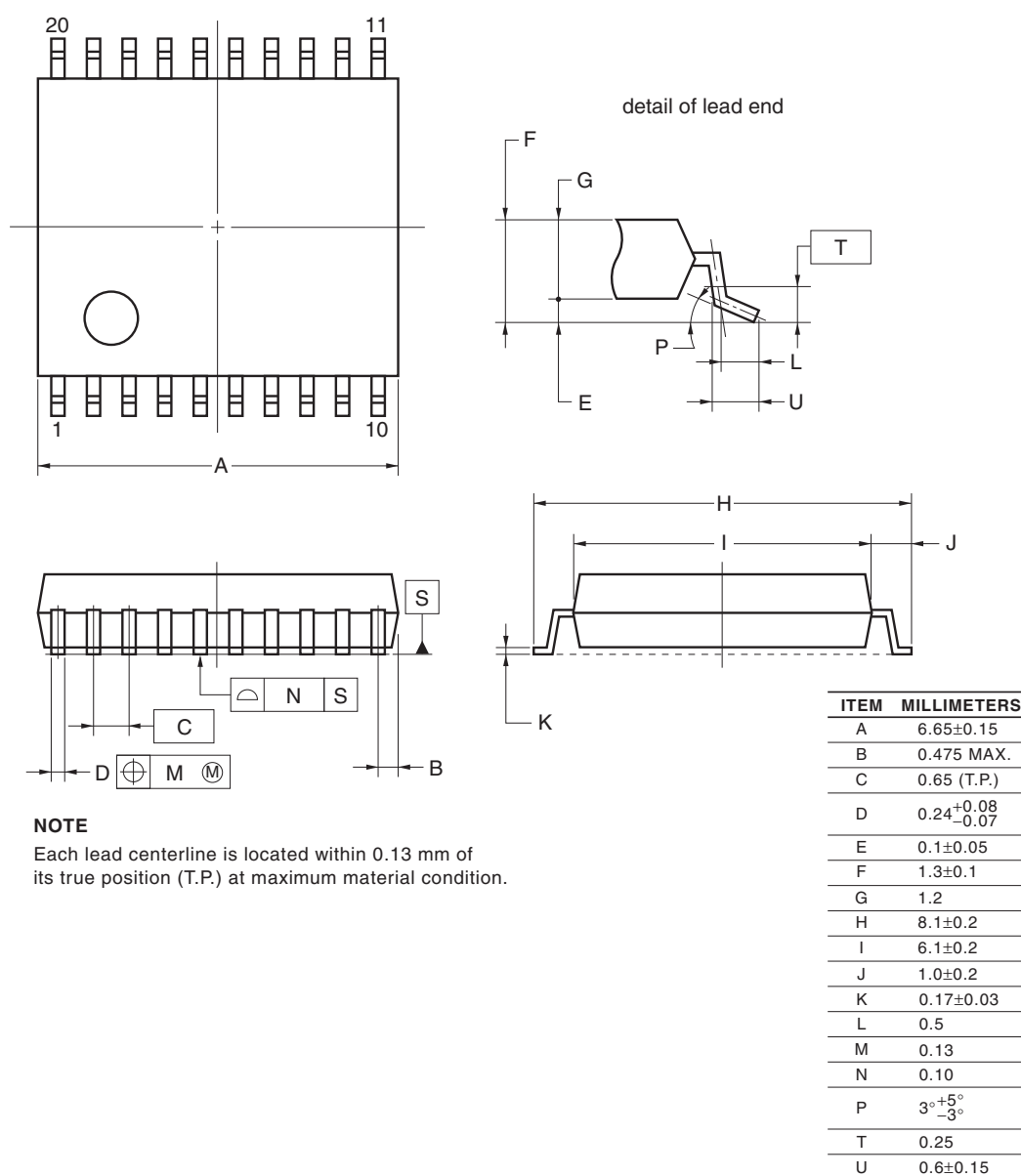
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V _{LVDD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage		2.64	2.75	2.86	V
	V _{LVDD1}	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	V _{LVDD2}	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	V _{LVDD3}	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

4. PACKAGE DRAWINGS

4.1 20-pin Products

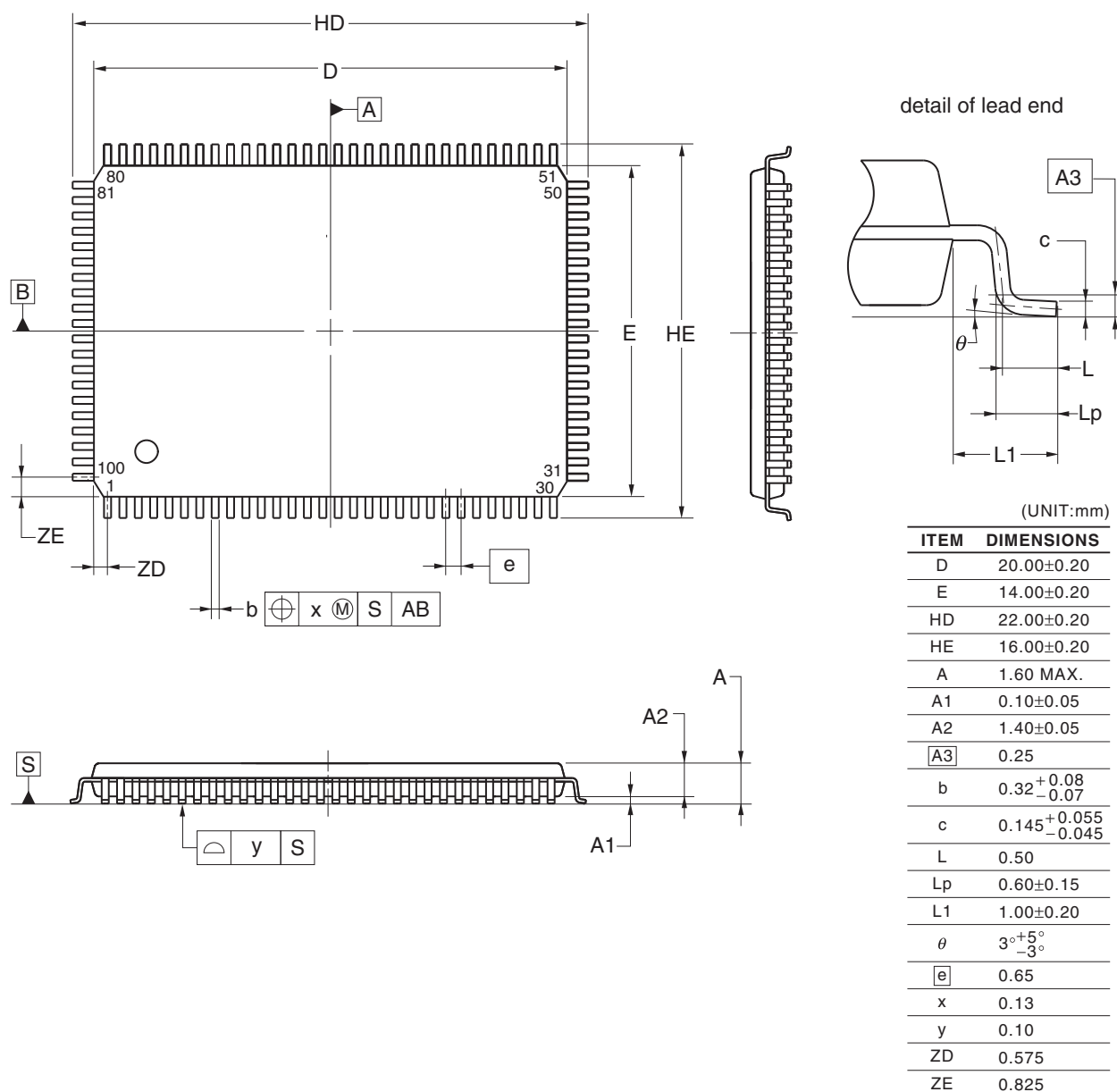
R5F1006AASP, R5F1006CASP, R5F1006DASP, R5F1006EASP
 R5F1016AASP, R5F1016CASP, R5F1016DASP, R5F1016EASP
 R5F1006ADSP, R5F1006CDSP, R5F1006DDSP, R5F1006EDSP
 R5F1016ADSP, R5F1016CDSP, R5F1016DDSP, R5F1016EDSP
 R5F1006AGSP, R5F1006CGSP, R5F1006DGSP, R5F1006EGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-0300-0.65	PLSP0020JC-A	S20MC-65-5A4-3	0.12



R5F100PFAFA, R5F100PGAFA, R5F100PHAFA, R5F100PJFAFA, R5F100PKAFA, R5F100PLAFA
 R5F101PFAFA, R5F101PGAFA, R5F101PHAFA, R5F101PJFAFA, R5F101PKAFA, R5F101PLAFA
 R5F100PFDFA, R5F100PGDFA, R5F100PHDFA, R5F100PJDFA, R5F100PKDFA, R5F100PLDFA
 R5F101PFDFA, R5F101PGDFA, R5F101PHDFA, R5F101PJDFA, R5F101PKDFA, R5F101PLDFA
 R5F100PFGFA, R5F100PGGFA, R5F100PHGFA, R5F100PJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



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